74AHC3G14-Q100; 74AHCT3G14-Q100

Triple inverting Schmitt trigger

Rev. 3 — 16 September 2013 Product data sheet

1. General description

74AHC3G14-Q100 and 74AHCT3G14-Q100 are high-speed Si-gate CMOS devices. They provide three inverting buffers with Schmitt trigger action. These devices are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Applications

- Wave and pulse shaper for highly noisy environment
- Astable multivibrator
- Monostable multivibrator

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC3G14DP-Q100	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHCT3G14DP-Q100				
74AHC3G14DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AHCT3G14DC-Q100				
74AHC3G14GD-Q100	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT996-2
74AHCT3G14GD-Q100				

5. Marking

Table 2. Marking codes

Type number	Marking code[1]
74AHC3G14DP-Q100	A14
74AHCT3G14DP-Q100	C14
74AHC3G14DC-Q100	A14
74AHCT3G14DC-Q100	C14
74AHC3G14GD-Q100	A14
74AHCT3G14GD-Q100	C14

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram

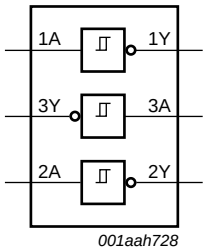


Fig 1. Logic symbol

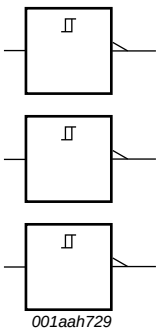


Fig 2. IEC logic symbol

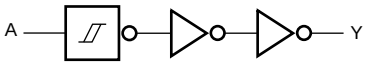


Fig 3. Logic diagram (one Schmitt trigger)

7. Pinning information

7.1 Pinning

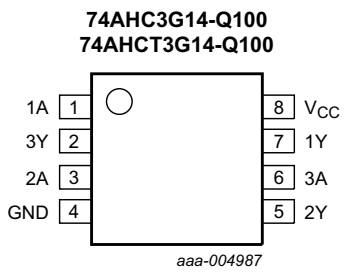


Fig 4. Pin configuration SOT505-2 and SOT765-1

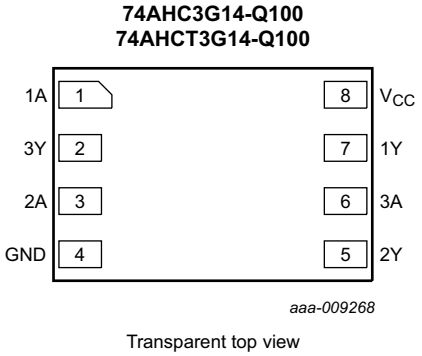


Fig 5. Pin configuration SOT996-2

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V_{CC}	8	supply voltage

8. Functional description

Table 4. Function table [1]

Input nA	Output nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7.0	V
V_I	input voltage			−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V		−20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	75	mA
I_{GND}	ground current			−75	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly at 8 mW/K.
For XSON8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC3G14-Q100			74AHCT3G14-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	+25	+125	−40	+25	+125	°C

11. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC3G14-Q100										
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}								
		I_O = –50 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 μA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}								
		I_O = 50 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.0	-	10	-	40	μA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT3G14-Q100										
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}; V_{CC} = 4.5 V								
		I_O = –50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}; V_{CC} = 4.5 V								
		I_O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.0	-	10	-	40	μA
ΔI_{CC}	additional supply current	per input pin; V_I = 3.4 V; other inputs at V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF

11.1 Transfer characteristics

Table 8. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V). See Figure 8 and Figure 9.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC3G14-Q100										
V_{T+}	positive-going threshold voltage	V_{CC} = 3.0 V	-	-	2.2	-	2.2	-	2.2	V
		V_{CC} = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
		V_{CC} = 5.5 V	-	-	3.85	-	3.85	-	3.85	V
V_{T-}	negative-going threshold voltage	V_{CC} = 3.0 V	0.9	-	-	0.9	-	0.9	-	V
		V_{CC} = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
		V_{CC} = 5.5 V	1.65	-	-	1.65	-	1.65	-	V
V_H	hysteresis voltage	V_{CC} = 3.0 V	0.3	-	1.2	0.3	1.2	0.25	1.2	V
		V_{CC} = 4.5 V	0.4	-	1.4	0.4	1.4	0.35	1.4	V
		V_{CC} = 5.5 V	0.5	-	1.6	0.5	1.6	0.45	1.6	V
74AHCT3G14-Q100										
V_{T+}	positive-going threshold voltage	V_{CC} = 4.5 V	-	-	2.0	-	2.0	-	2.0	V
		V_{CC} = 5.5 V	-	-	2.0	-	2.0	-	2.0	V
V_{T-}	negative-going threshold voltage	V_{CC} = 4.5 V	0.5	-	-	0.5	-	0.5	-	V
		V_{CC} = 5.5 V	0.6	-	-	0.6	-	0.6	-	V
V_H	hysteresis voltage	V_{CC} = 4.5 V	0.4	-	1.4	0.4	1.4	0.35	1.4	V
		V_{CC} = 5.5 V	0.4	-	1.6	0.4	1.6	0.35	1.6	V

12. Dynamic characteristics

Table 9. Dynamic characteristics

GND = 0 V; $t_r = t_f \leq 3.0$ ns; for test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
74AHC3G14-Q100											
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C_L = 15 pF		-	4.2	12.8	1.0	15.0	1.0	16.5	ns
		C_L = 50 pF		-	6.0	16.3	1.0	18.5	1.0	20.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.2	8.6	1.0	10.0	1.0	11.0	ns
		C_L = 50 pF		-	4.6	10.6	1.0	12.0	1.0	13.5	ns
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	10	-	-	-	-	-	pF

Table 9. Dynamic characteristics *...continued*

GND = 0 V; $t_r = t_f \leq 3.0$ ns; for test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
74AHCT3G14-Q100											
t_{pd}	propagation delay	nA to nY; V_{CC} = 4.5 V to 5.5 V	[1] [3]								
		C_L = 15 pF		-	4.1	7.0	1.0	8.0	1.0	9.0	ns
		C_L = 50 pF		-	5.9	8.5	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	12	-	-	-	-	-	pF

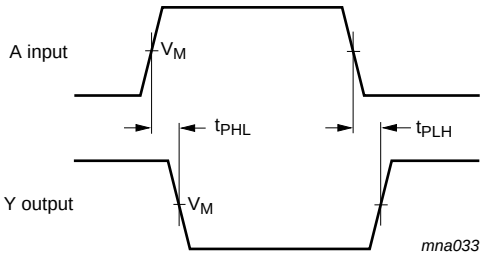
[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at V_{CC} = 5.0 V.

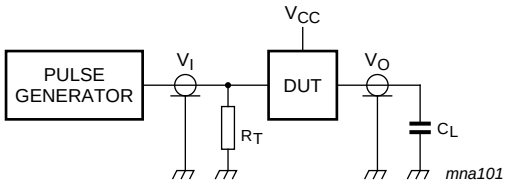
[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms



The test data is given in Table 10

Fig 6. The input (nA) to output (nY) propagation delays



Test data is given in Table 10.

Definitions for test circuit:

C_L = Load capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type number	Input		Output
	V_I	V_M	V_M
74AHC3G14-Q100	GND to V_{CC}	0.5 × V_{CC}	0.5 × V_{CC}
74AHCT3G14-Q100	GND to 3.0 V	1.5 V	0.5 × V_{CC}

13.1 Transfer characteristic waveforms

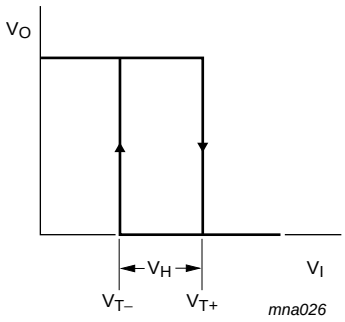


Fig 8. Transfer characteristic

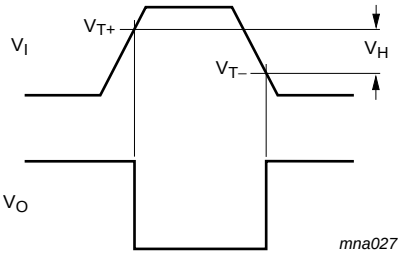
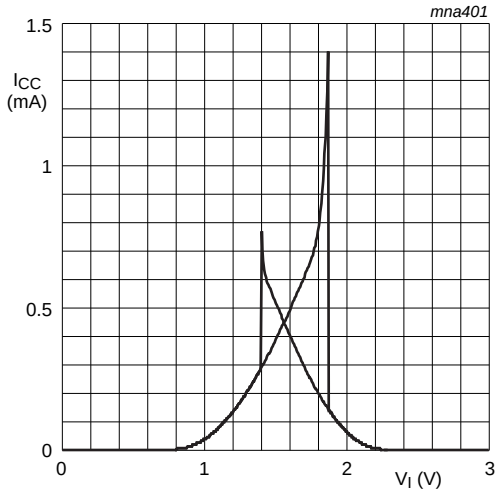
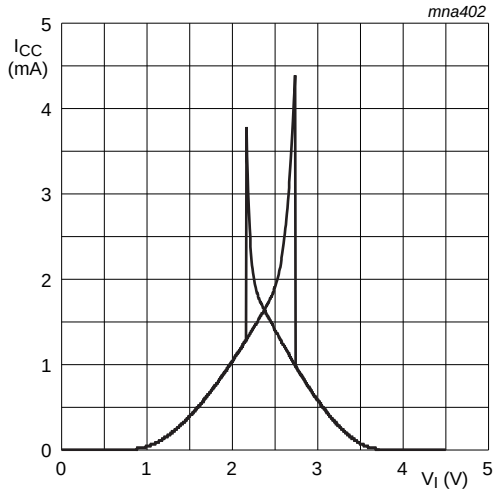


Fig 9. The definitions of V_{T+}, V_{T-} and V_H



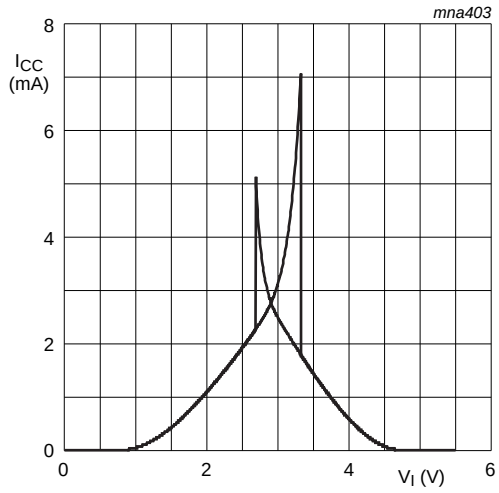
V_{CC} = 3.0 V.

Fig 10. Typical 74AHC3G14-Q100 transfer characteristics



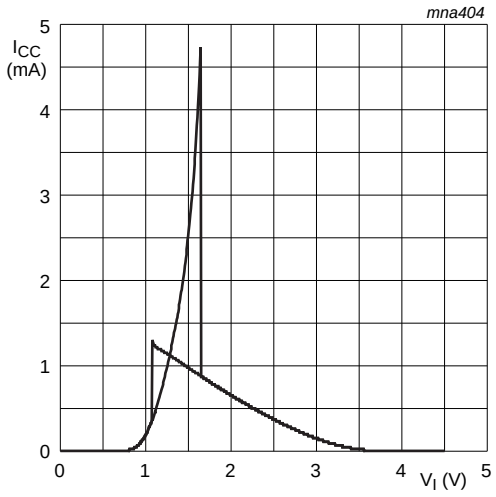
V_{CC} = 4.5 V.

Fig 11. Typical 74AHC3G14-Q100 transfer characteristics



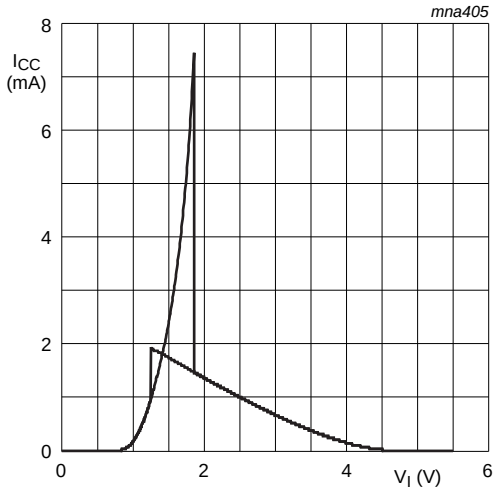
V_{CC} = 5.5 V.

Fig 12. Typical 74AHC3G14-Q100 transfer characteristics



V_{CC} = 4.5 V.

Fig 13. Typical 74AHCT3G14-Q100 transfer characteristics



V_{CC} = 5.5 V.

Fig 14. Typical 74AHCT3G14-Q100 transfer characteristics

14. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$ where:

P_{add} = additional power dissipation (μW);

f_i = input frequency (MHz);

t_r = input rise time (ns); 10 % to 90 %;

t_f = input fall time (ns); 90 % to 10 %;

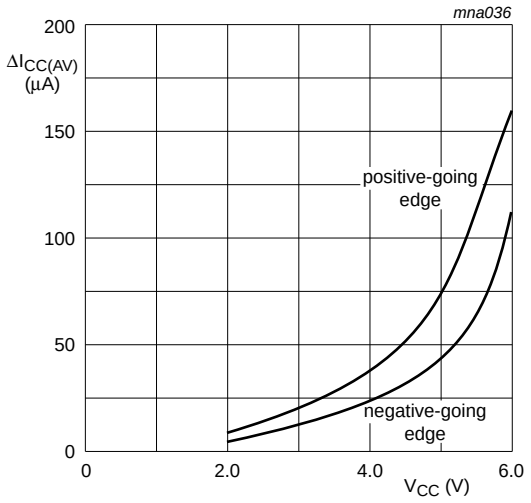
$\Delta I_{CC(AV)}$ = average additional supply current (μA).

$\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in Figure 15 and Figure 16.

For 74AHC3G14-Q100 and 74AHCT3G14-Q100 used in relaxation oscillator circuit, see Figure 17.

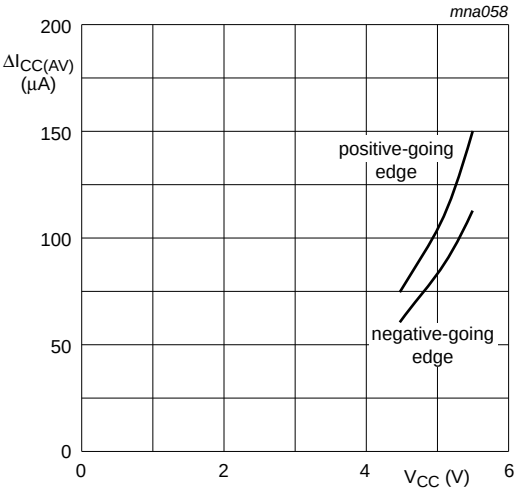
Note to the application information:

1. All values given are typical unless otherwise specified.



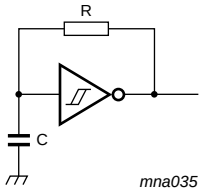
Linear change of V_I between $0.1V_{CC}$ to $0.9V_{CC}$

Fig 15. Average additional I_{CC} for 74AHC3G14-Q100 Schmitt trigger devices



Linear change of V_I between $0.1V_{CC}$ to $0.9V_{CC}$

Fig 16. Average additional I_{CC} for 74AHCT3G14-Q100 Schmitt trigger devices



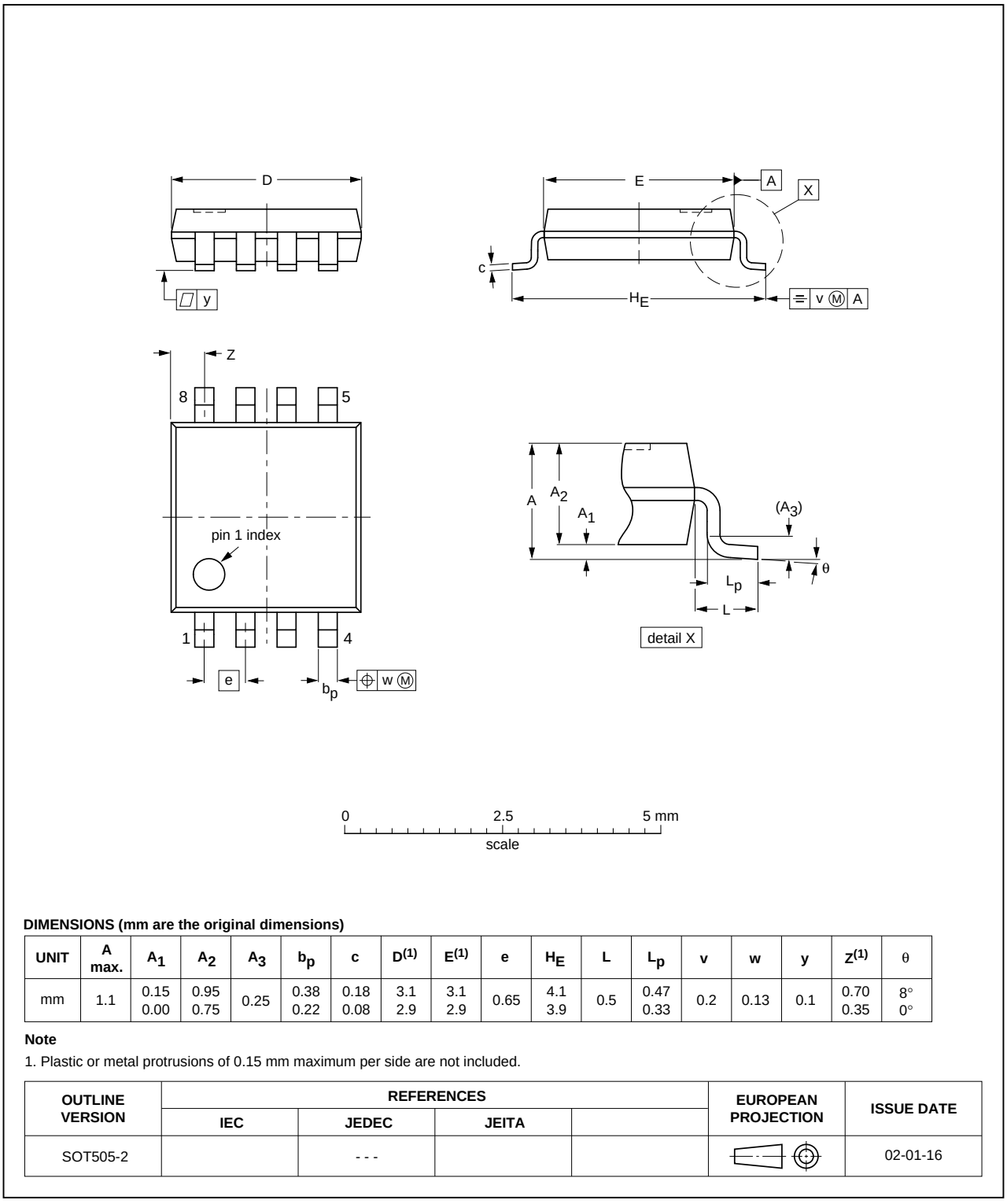
For 74AHC3G14-Q100: $f = \frac{1}{T} \approx \frac{1}{0.55 \times RC}$

For 74AHCT3G14-Q100: $f = \frac{1}{T} \approx \frac{1}{0.60 \times RC}$

Fig 17. Relaxation oscillator using the 74AHC3G14-Q100 and 74AHCT3G14-Q100

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

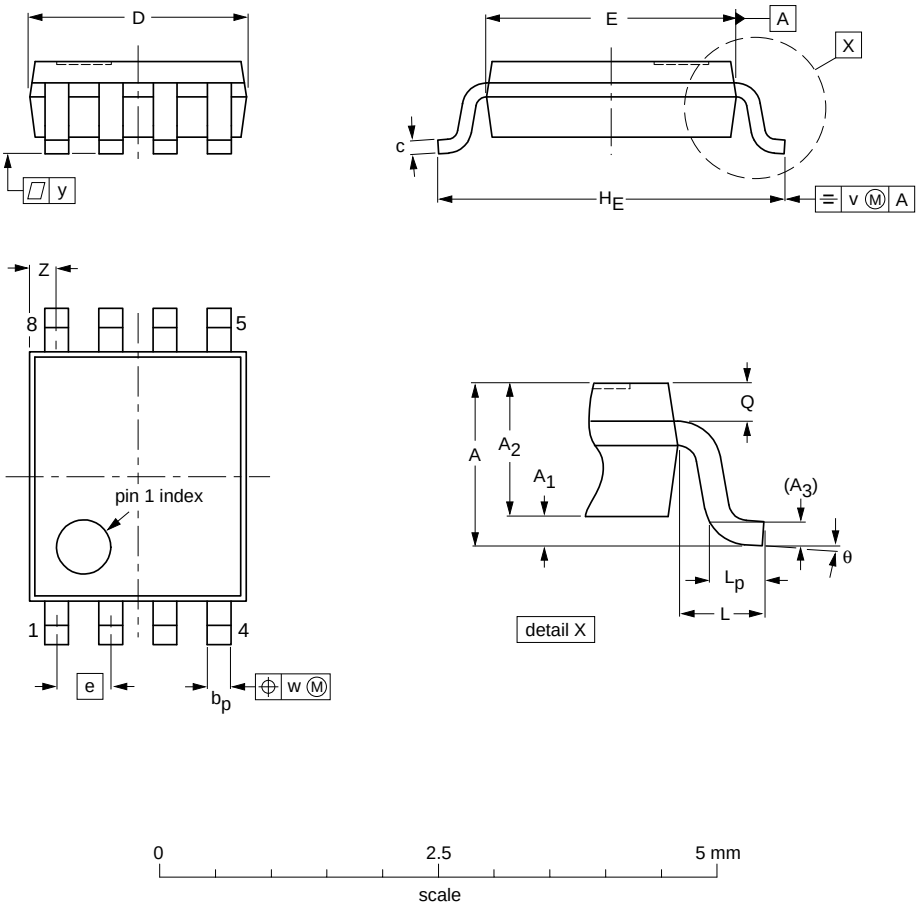
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 18. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

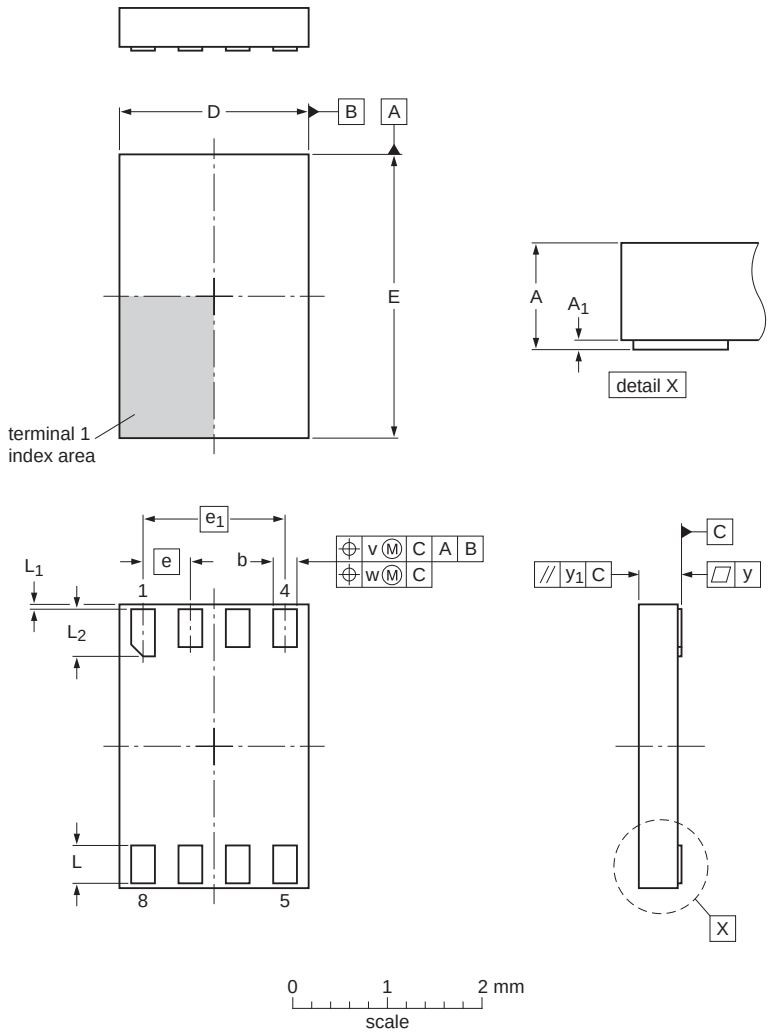
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 19. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm **SOT996-2**



Dimensions (mm are the original dimensions)

Unit[1]		A	A_1	b	D	E	e	e_1	L	L_1	L_2	v	w	y	y_1
	max		0.05	0.35	2.1	3.1			0.5	0.15	0.6				
mm	nom	0.5					0.5	1.5				0.1	0.05	0.05	0.1
	min		0.00	0.15	1.9	2.9			0.3	0.05	0.4				

sot996-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT996-2						~~07-12-21~~ 12-11-20

Fig 20. Package outline SOT996-2 (XSON8)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT3G14_Q100 v.3	20130916	Product data sheet	-	74AHC_AHCT3G14_Q100 v.2
Modifications:	• Added type number 74AHC3G14GD-Q100 and 74AHCT3G14GD-Q100.			
74AHC_AHCT3G14_Q100 v.2	20130128	Product data sheet	-	74AHC_AHCT3G14_Q100 v.1
74AHC_AHCT3G14_Q100 v.1	20121001	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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20. Contents

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